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12-302

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q65781

Hiroyuki NAGASAWA

Appln. No.: 09/924,872

Group Art Unit: 2812

Confirmation No.: 3695

Examiner: S. MULPURI

Filed: August 09, 2001

For: SILICON CARBIDE AND METHOD OF MANUFACTURING THE SAME

**SUPPLEMENTAL AMENDMENT UNDER 37 C.F.R. § 1.111**

Commissioner for Patents  
Washington, D.C. 20231

Sir:

This is in response to the Examiner's telephone call to the Applicant's representative on November 13, 2002, indicating that claim 14, which previously had been indicated as allowable, would be rejected unless amended to incorporate limitations similar to those that appear in claim 15. In order to obtain allowance of this case, please further amend the above-identified application as follows:

**IN THE CLAIMS**

**Please enter the following amended claim:**

14. (Amended) A silicon carbide having a region which has an impurity concentration gradient between  $1 \times 10^{22}/\text{cm}^4$  and  $4 \times 10^{24}/\text{cm}^4$  in the thickness direction, said silicon carbide being manufactured by the method comprising:

depositing silicon from a vapor phase or a liquid phase onto a substrate and forming a silicon layer on the substrate;

doping the silicon layer with an impurity composed of at least one element selected from a group consisting of N, B, Al, Ga, In, P, As, Sb, Se, Zn, O, Au, V, Er, Ge, and Fe, to form a doped silicon layer; and